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b1
c1
an interlayer insulating film covering said thin film transistor and said plurality of projected portions, said interlayer insulating film having a projected and recessed surface, and said interlayer insulating film comprising a resin film having a viscosity of 10 cp or more; and a pixel electrode electrically connected to said thin film transistor, said pixel electrode having a projected and recessed surface on said interlayer insulating film.

b2
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10.(Amended) A semiconductor device comprising:

a thin film transistor comprising a semiconductor layer on an insulating surface, an insulating film on said semiconductor layer and a gate electrode on said insulating film;
a plurality of projected portions on said insulating surface;
an interlayer insulating film covering said thin film transistor and said plurality of projected portions, said interlayer insulating film having a projected and recessed surface, and said interlayer insulating film comprising a resin film having a viscosity of 10 cp or more; and a pixel electrode having a projected and recessed surface on said interlayer insulating film, and electrically connected to said thin film transistor.

b3
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19.(Amended) A semiconductor device comprising:

a thin film transistor comprising a semiconductor layer over a substrate and a gate electrode with an insulating film interposed therebetween;
a plurality of projected portions over said substrate;
an interlayer insulating film covering said thin film transistor and said plurality of projected portions, said interlayer insulating film having a projected and recessed surface, and said interlayer insulating film comprising a resin film having a viscosity of 10 cp or more; and

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a pixel electrode electrically connected to said thin film transistor, said pixel electrode having a projected and recessed surface on said interlayer insulating film.

27.(Amended) A semiconductor device comprising:

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a thin film transistor comprising a semiconductor layer on an insulating surface, an insulating film on said semiconductor layer and a gate electrode on said insulating film;

a plurality of projected portions on said insulating film;

an interlayer insulating film covering said thin film transistor and said plurality of projected portions, said interlayer insulating film having a projected and recessed surface, and said interlayer insulating film comprising a resin film having a viscosity of 10 cp or more; and

a pixel electrode having a projected and recessed surface on said interlayer insulating film, and electrically connected to said thin film transistor.

28.(Amended) The semiconductor device according to claim 27, wherein said projected portions comprise a same material as a gate electrode of said thin film transistor.

REMARKS

Applicants will address each of the Examiner's rejections in the order in which they appear in the Office Action.

Claim Rejection – 35 USC §112

In the Office Action, the Examiner rejects Claim 28 under 35 USC 112, second paragraph, as being indefinite. In order to advance the prosecution of this application,